

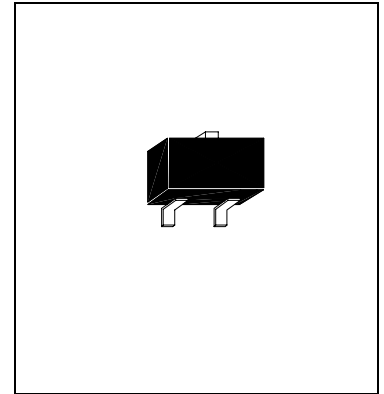


MMBT4403LT1

PNP EPITAXIAL PLANAR TRANSISTOR

Description

The MMBT4403LT1 is designed for general purpose applications requiring high breakdown voltages.



Absolute Maximum Ratings

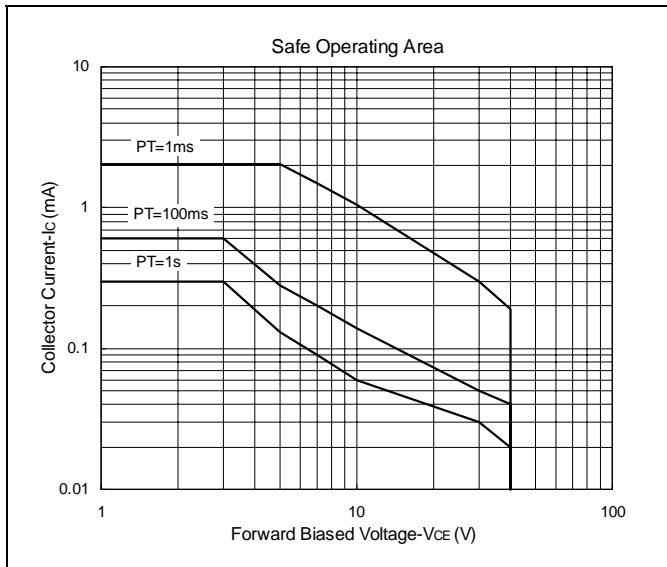
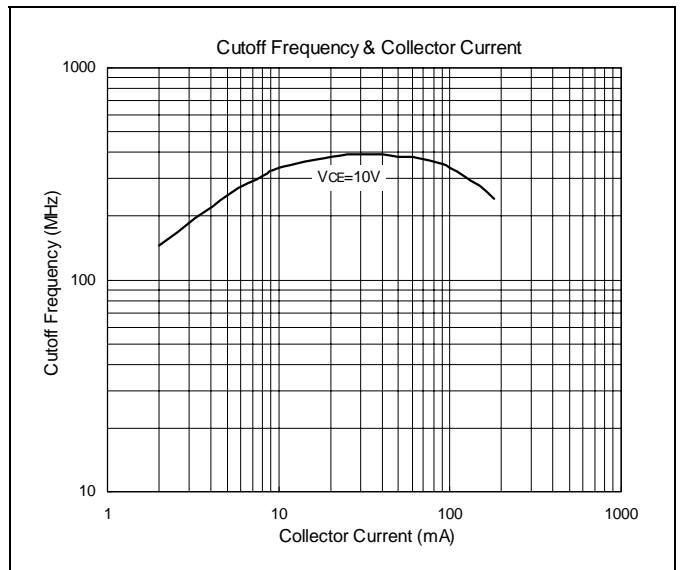
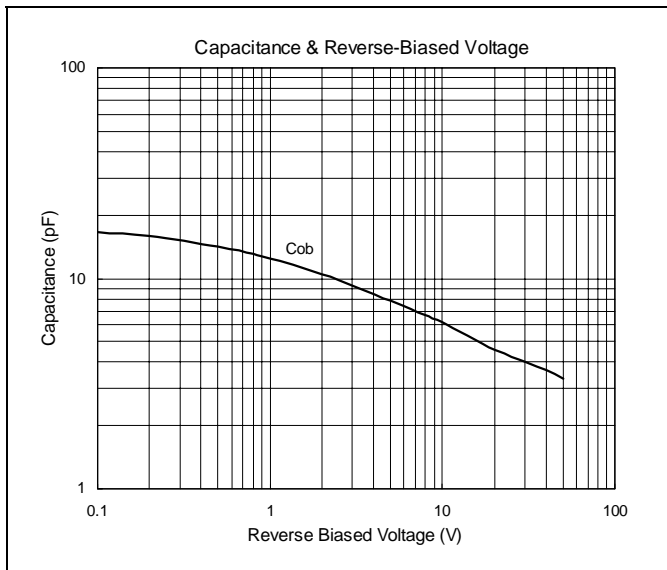
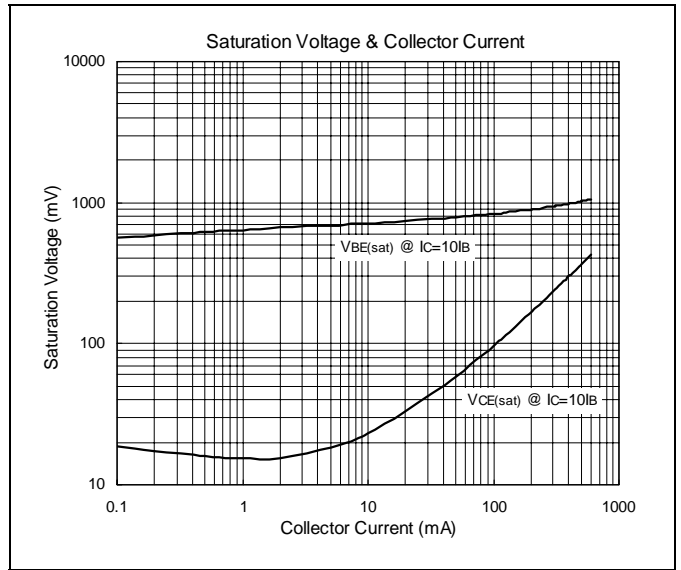
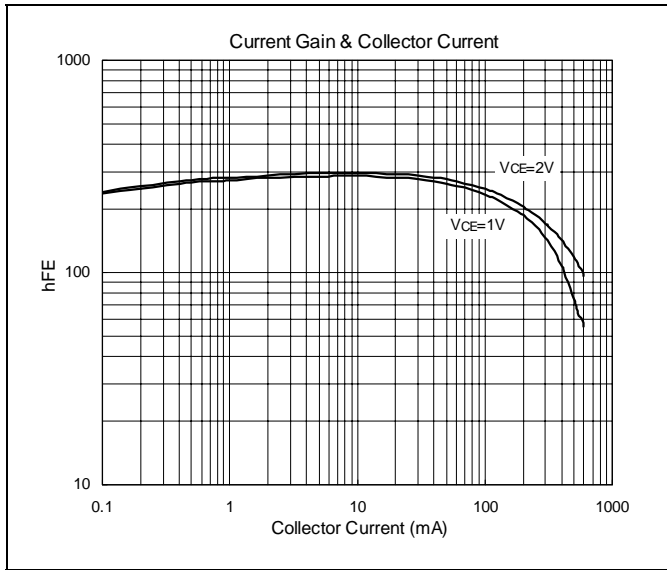
- Maximum Temperatures
Storage Temperature..... -55~+150°C
Junction Temperature..... +150°C
- Maximum Power Dissipation
Total Power Dissipation (Ta=25°C) 250 mW
- Maximum Voltages and Currents (Ta=25°C)
VCBO Collector to Base Voltage 40 V
VCEO Collector to Emitter Voltage 40 V
VEBO Emitter to Base Voltage 5.0 V
IC Collector Current 600 mA

Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	40	-	-	V	IC=100uA
BVCEO	40	-	-	V	IC=1mA
BVEBO	5.0	-	-	V	IE=100uA
ICEX	-	-	100	nA	VCE=35V, VBE=0.4V
VCE(sat)1	-	-	400	mV	IC=150mA, IB=15mA
VCE(sat)2	-	-	750	mV	IC=500mA, IB=50mA
VBE(sat)1	-	-	950	mV	IC=150mA, IB=15mA
VBE(sat)2	-	-	1.3	V	IC=500mA, IB=50mA
hFE1	30	-	-		VCE=1V, IC=0.1mA
hFE2	60	-	-		VCE=1V, IC=1mA
hFE3	100	-	-		VCE=1V, IC=10mA
hFE4	100	-	300		VCE=2V, IC=150mA
hFE5	20	-	-		VCE=2V, IC=500mA
fT	200	-	-	MHz	VCE=10V, IC=20mA, f=100MHz
Cob	-	-	8.5	pF	VCB=10V, f=1MHz

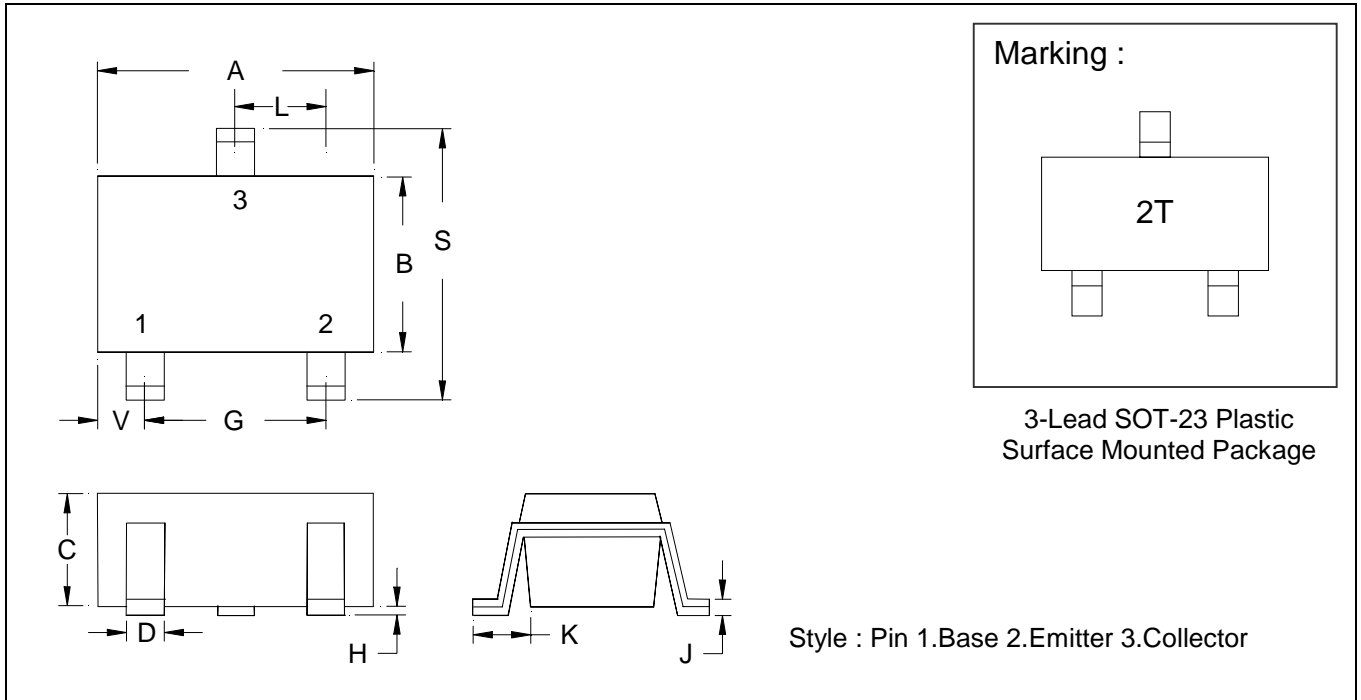


Characteristics Curve





SOT-23 Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.118	2.80	3.00	J	0.0035	0.0043	0.09	0.11
B	0.0550	0.0630	1.40	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0354	0.0512	0.90	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0886	0.1083	2.25	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	-	0.0040	-	0.10					